

Fast recovery Diode

RF101L2S

●Applications

High frequency rectification

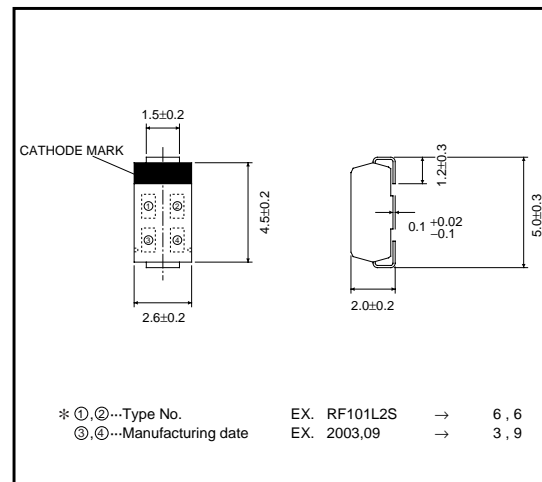
●Features

- 1) Small power mold type (PMDS)
- 2) Ultra low VF
- 3) Very fast recovery
- 4) Low switching loss

●Construction

Silicon epitaxial planar

●External dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V _{RM}	200	V
Reverse voltage (DC)	V _R	200	V
Average rectified forward current *	I _O	1.0	A
Forward peak surge current (60Hz · 1cyc.)	I _{FSM}	20	A
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Mounting on glass epoxy board

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Typ.	Max.	Unit	Conditions
Forward voltage	V _F	0.815	0.870	V	I _F =1.0A
Reverse current	I _R	10n	10μ	A	V _R =200V
Reverse recovery time	t _{rr}	12	25	nS	I _F =0.5A
					I _R =1.0A
					I _{rr} =0.25 × I _R

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta=25°C)

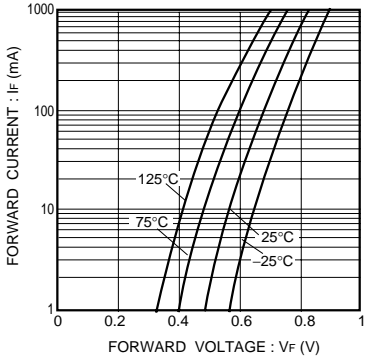


Fig.1 Forward temperature characteristics

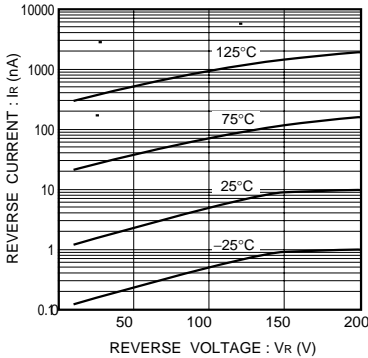


Fig.2 Reverse temperature characteristics

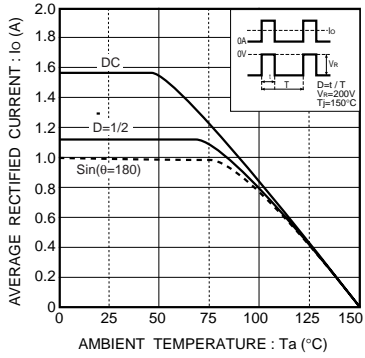


Fig.3 Derating curve

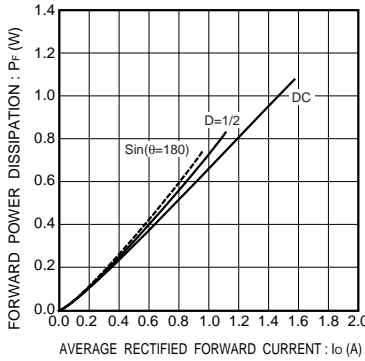


Fig. 4 Power dissipation characteristics

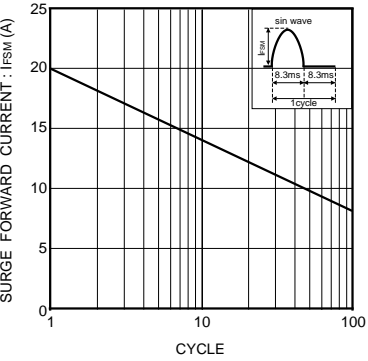


Fig.5 Forward peak surge current

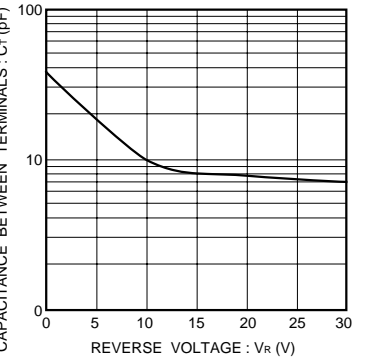


Fig. 6 Capacitance between terminals characteristics

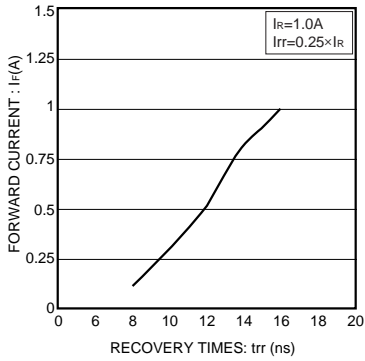


Fig. 7 Reverse recovery time